L Number	Hits	Search Text	DB	Time stamp
1	45	(SAC or "self aligned contact") and ArF	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:18
2	95	(opening or trench) and (resist or photoresist) and ("antireflective" or ARC or BARC) and (fluorocarbons or hydrofluorocarbons)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:07
3	130	(opening or trench or contact) and (resist or photoresist) and ("antireflective" or ARC or BARC) and (fluorocarbons or hydrofluorocarbons)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:08
4	680	(opening or trench or contact) and (resist or photoresist) and ("silicon oxide" or "SiO.sub.2") and (SiN or "silicon nitride") and (SiON or "silicon oxynitride") and (CF4 or "CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2")	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:12
5	477	((opening or trench or contact) and (resist or photoresist) and ("silicon oxide" or "SiO.sub.2") and (SiN or "silicon nitride") and (SiON or "silicon oxynitride") and (CF4 or "CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2")) and 438/$.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:26
6	870	(opening or trench or contact) and (resist or photoresist) and ("silicon oxide" or "SiO.sub.2") and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2")	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:22
7	4977	((438/706) or (438/710) or (438/712) or (438/714) or (438/720)).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:13
9	98	((opening or trench or contact) and (resist or photoresist) and ("silicon oxide" or "SiO.sub.2") and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2")) and (((438/706) or (438/710) or (438/712) or (438/714) or (438/720)).CCLS.)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:14
10	45	(opening or trench or contact) and (resist or photoresist) and ("silicon oxide" or "SiO.sub.2") and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2") and pattern$4 and ArF	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:14
12	5	(opening or trench or contact) and (resist or photoresist) and ("silicon oxide" or "SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4") and (CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2")	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:18
15	1086	(opening or trench or contact) and (resist or photoresist or pattern$4) and ("silicon oxide" or "SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2")	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:20

16	104	(SAC or "self aligned contact") and ((opening or trench or contact) and (resist or photoresist or pattern$4) and ("silicon oxide" or "SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2"))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:18
17	33	(CF4 or "CF.sub.4") same (CH2F2 or "CH.sub.2F.sub.2" or hydrofluorocarbon) same (oxygen or "O.sub.2")	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:21
18	597	(opening or trench or contact) and (resist or photoresist) and ("silicon oxide" or "SiO.sub.2") and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2") and gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:25
19	618	(opening or trench or contact) and pattern$4 and ("silicon oxide" or "SiO.sub.2") and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2") and gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:26
20	430	((opening or trench or contact) and pattern$4 and ("silicon oxide" or "SiO.sub.2") and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2") and gate) and 438/$.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:26